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AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A process for producing a microswitch, comprising at least the following steps:

producing a first subassembly having a first substrate and at least conducting lines and a control electrode, the substrate having regions of additional thickness, called mesas, and a second conducting layer, each mesa being covered with a thickness of metal identical to that of the conducting lines;

producing a second subassembly having a second substrate, at least one stop layer, a layer of material, at least one electrically conducting layer and at least one high-permittivity layer;

assembling the two subassemblies mechanical and electrical;

eliminating the second substrate down to the stop layer; and

final cutting of the layer to the dimensions of a membrane by photolithography and etching.

2. (Previously Presented) The process for producing a microswitch as claimed in claim 1, wherein the high-permittivity layer is deposited by a sputtering or sol-gel process.

3. (Canceled)

4. (Currently Amended) The process for producing a microswitch as claimed in claim [[3]] 1, wherein the conducting layer has, facing the mesas, regions of additional

thickness that are produced in the same material as the layer and have the same thickness.

5. (Currently Amended) The process for producing a microswitch as claimed in claim [[3]] 1, wherein, for a parallel-type microswitch comprising, on the first subassembly, two conducting lines located on the insulating substrate, which are mutually parallel and electrically connected to an electrical ground; a conducting line, called the input signal line which is placed between the ground lines and is parallel to said ground lines; a conducting line called the output signal line which is placed in the extension of the input signal line and between the ground lines, which is parallel to said ground lines and a control electrode located on said substrate, one of the ends of which electrically connects the input signal line and the output signal line, and the two subassemblies are joined together by the deposition and bonding of a eutectic alloy)]] between the ground lines and the conducting layers, the regions of additional thickness resting on the mesas.

6. (Previously Presented) The process for producing a microswitch as claimed in claim 5, wherein the eutectic alloy is of the gold/tin type.

7. (Previously Presented) The process for producing a microswitch as claimed in claim 1, wherein at least one deposition of deformable metal is carried out on the first subassembly.

8. (Previously Presented) The process for producing a microswitch as claimed in claim 7, wherein the deformable material is either gold or a gold/tin eutectic alloy.

9. (Previously Presented) The process for producing a microswitch as claimed in claim 7, wherein the production of the second subassembly comprises the following substeps:

producing an assembly having the first substrate, at least the stop layer and the

layer of material;

cutting of the layer so as to create at least one pillar; and

deposition of the electrically conducting layer and at least the layer on the layer.

10. (Previously Presented) The process for producing a microswitch as claimed in claim 7, wherein the second subassembly is joined to the first subassembly by anodic bonding at its pillar or pillars.

11. (Previously Presented) The process for producing a microswitch as claimed in claim 7, wherein in the case of a parallel-type switch, the electrical connection between the ground lines and the conducting layers is produced by means of the deposit or deposits of metal.

12. (Previously Presented) The process for producing a plurality of microswitches as claimed in claim 1, wherein a plurality of subassemblies are produced on a common substrate and a plurality of subassemblies are produced on a common substrate, the joining operation being common to the two subassemblies, the whole assembly obtained then being cut in order to obtain a plurality of individual microswitches.

13. (Previously Presented) The process for producing a microswitch as claimed in claim 8, wherein in the case of a parallel-type switch, the electrical connection between the ground lines and the conducting layers is produced by means of the deposit or deposits of metal.

14. (Previously Presented) The process for producing a microswitch as claimed in claim 9, wherein in the case of a parallel-type switch, the electrical connection between the ground lines and the conducting layers is produced by means of the deposit or deposits of metal.

15. (Previously Presented) The process for producing a microswitch as claimed in claim 10, wherein in the case of a parallel-type switch, the electrical connection between the ground lines and the conducting layers is produced by means of the deposit or deposits of metal.